disclaimer, amends claims 1 and 7 to further clarify the nature of his invention, and respectfully traverses the rejection under 35 U.S.C. §103(a).

Im et al. discloses processing carried out by iteratively (1) irradiating a sample at an energy density sufficient to induce complete melting of the silicon film in the exposed areas and (2) translating relative to the beam over a distance approximately one-half of the single-pulse lateral growth distance, (p. 3434, right column, second paragraph). However, such processing is made using just a submicrometer-precision translation stage, (p. 3434, right column, lines 8-9). Im et al. does **not** refer to usage of an alignment mark on a substrate as claimed herein, in spite of the fact that Im et al. describes the idea of fabricating a single-crystal Si TFT device on the substrate.

The Examiner suggests that the first chevron serves as the alignment mark for the other chevrons as shown in Fig. 1 of Im et al. However, as described on page 3435, left column, line 19, the number and relative location of the regions shown in Fig. 1 can be precisely controlled by using an appropriately patterned mask. Accordingly, it is apparent that many chevrons as shown in Fig. 1 are simultaneously formed and one does not serve as an alignment mark for the other ones.

Fig. 1 of Im et al. shows a defect-etched SLS-processed film. In contrast, a film before defect-etching has a different appearance than Fig. 1.

Adachi et al. discloses that an insulation film is formed over one type of Si film. In contrast, according to the present invention an insulation film is formed over two types of Si films, namely, a first-property semiconductor film, and a second-property semiconductor film.

CONCLUSION

An earnest effort has been made to be fully responsive to the Examiner's objections. In view of the above amendments and remarks, it is believed that independent claims 1 and 7 are in condition for allowance, as well as the claims dependent therefrom. Passage of this case to allowance is earnestly solicited.

However, if for any reason the Examiner should consider this application not to be in condition for allowance, he is respectfully requested to telephone the undersigned attorney at the number listed below prior to issuing a further Action.

Attached is a marked-up version of the changes made to the claims by the current amendment. The attached pages are captioned **"Version With Marks To Show Changes Made".**

Any fee due with this paper, not fully covered by an enclosed check, may be charged on Deposit Account 50-1290.

Respectfully submitted,

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Enclosure: Version With Markings To Show Changes Made

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS

Please amend claims 1 and 7 as follows:

1. (Thrice Amended) A method for forming a first-property semiconductor film at a desired position on a substrate, comprising the steps of:

a) preparing the substrate having a second-property semiconductor film formed [thereon;] thereon, wherein the substrate has an alignment mark previously formed thereon;

b) preparing an optical mask having a predetermined pattern on another substrate which is apart from the substrate;

c) relatively positioning a projection area of the optical mask at the desired position on the [substrate;] substrate by using the alignment mark as a reference;

d) irradiating the desired position of the second-property semiconductor film with laser light through the optical mask to change an irradiated portion of the second-property semiconductor film to the first-property semiconductor film; and

e) forming an insulation film on the first-property semiconductor film and the second-property semiconductor film.

7. (Thrice Amended) A method for forming a crystalline semiconductor film at a desired position on a substrate, comprising the steps of:

a) preparing the substrate having an amorphous semiconductor film formed [thereon;] thereon, wherein the substrate has an alignment mark previously formed thereon;

b) preparing an optical mask having a predetermined pattern on another substrate which is apart from the substrate;

c) relatively positioning a projection area of the optical mask at the desired position on the [substrate;] substrate by using the alignment mark as a reference;

d) irradiating the desired position of the amorphous semiconductor film with laser light through the optical mask to change an irradiated portion of the amorphous semiconductor film to the crystalline semiconductor film; and

e) forming an insulation film on the crystalline semiconductor film and the amorphous semiconductor film.